This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-40. (cancelled)

Claim 41. (previously presented) A single crystal silicon wafer having a central axis, a front side and a back side which are generally perpendicular to the axis, a circumferential edge, and a radius extending from the central axis to the circumferential edge of the wafer, the wafer comprising:

a nominal diameter of about 300 mm;

an axially symmetric region having no detectible agglomerated intrinsic point defects at a detection limit of 10^3 defects/cm^3, the axially symmetric region extending radially inwardly from the circumferential edge of the wafer and having a width, as measured from the circumferential edge radially toward the center axis, which is at least about 40% the length of the radius of the wafer.

Claim 42. (previously presented) The wafer as set forth in claim 41 wherein the axially symmetric region is generally annular in shape and the wafer further comprises a generally cylindrical region wherein the cylindrical region is located radially inward of the axially symmetric region and the cylindrical region has crystal lattice vacancies as the predominant intrinsic point defect.

Claim 43. (previously presented) The wafer as set forth in claim 41 wherein the wafer has as oxygen content which is less than about 13 PPMA.

Claim 44. (previously presented) The wafer as set forth in claim 41 wherein the wafer has as oxygen content which is less than about 11 PPMA.

Claim 45. (previously presented) The wafer as set forth in claim 41 wherein the wafer has an absence of oxygen precipitate nucleation centers.

Claim 46. (previously presented) The wafer as set forth in claim 41 wherein the axially symmetric region extending radially inwardly from the circumferential edge of the wafer has a width, as measured from the circumferential edge radially toward the center axis, which is about equal to the length of the radius.

Claim 47. (previously presented) The wafer as set forth in claim 41 wherein the axially symmetric region extending radially inwardly from the circumferential edge of the wafer has a width, as measured from the circumferential edge radially toward the center axis, which is at least about 30% the length of the radius, wherein silicon self-interstitials are the predominant intrinsic point defect in the axially symmetric region.

Claim 48. (previously presented) A single crystal silicon ingot having a central axis, a seed-cone, an end-cone, and a constant diameter portion between the seed-cone and the end-cone having a circumferential edge and a radius extending from the central axis to the circumferential edge, and a nominal diameter of 300 mm, the single crystal silicon ingot being characterized in that, after the ingot is grown and cooled from the solidification temperature, the constant diameter portion contains an axially symmetric region having no detectable agglomerated intrinsic point defects at a detection limit of 10^3 defects/cm^3, wherein the axially symmetric region extends radially inwardly from a circumferential edge of the ingot, has a width as measured from the circumferential edge radially toward the central axis of the ingot which is at least about 30% the length of the radius of the constant diameter portion, and has a length as measured along the central axis of at least about 20% the length of the constant diameter portion of the ingot.

Claim 49. (previously presented) The single crystal silicon ingot as set forth in claim 48 wherein the length of the axially symmetric region is at least 40% the length of the constant diameter portion of the ingot.

Claim 50. (previously presented) The single crystal silicon ingot as set forth in claim 49 wherein the length of the axially symmetric region is at least 60% the length of the constant diameter portion of the ingot.

Claim 51. (previously presented) The single crystal silicon ingot as set forth in claim 48 wherein the axially symmetric region has a width which is at least about 60% the length of the radius of the constant diameter portion.

Claim 52. (previously presented) The single crystal silicon ingot as set forth in claim 51 wherein the axially symmetric region has a width which is at least about 80% the length of the radius of the constant diameter portion.

Claim 53. (previously presented) The single crystal silicon ingot as set forth in claim 48 wherein silicon self-interstitials are the predominant intrinsic point defect in the axially symmetric region.

Claims 54-72. (cancelled)

Claim 73. (previously presented) An epitaxial wafer, comprising a single crystal silicon substrate having a central axis, a front side and a back side which are generally perpendicular to the central axis, a circumferential edge, a radius extending from the central axis to the circumferential edge, and a nominal diameter of 300 mm, the substrate comprising an axially symmetric region having no detectable agglomerated intrinsic point defects at a detection limit of 10^3 defects/cm^3, the axially symmetric region extending radially inwardly from the circumferential edge has a width, as measured from the circumferential edge radially toward the center axis, which is at least about 30% the length of the radius, wherein silicon self-interstitials are the predominant intrinsic point defect in the axially symmetric region of the wafer, and an epitaxial layer which is deposited on the front side of the substrate.

Claim 74. (previously presented) The epitaxial wafer as set forth in claim 73 wherein the width of the axially symmetric region is at least about 40% the length of the radius.

Claim 75. (previously presented) The epitaxial wafer as set forth in claim 73 wherein the width of the axially symmetric region is at least about 60% the length of the radius.

Claim 76. (previously presented) The epitaxial wafer as set forth in claim 73 wherein the width of the axially symmetric region is at least about 80% the length of the radius.

Claim 77. (previously presented) The epitaxial wafer as set forth in claim 73 wherein the width of the axially symmetric region is about equal to the length of the radius.

Claims 78-89. (cancelled)